

Cross-Industry Reliability: Automotive Power Module Perspective

Zhenxian Liang

R&D Staff

Power Electronics and Electric Machinery Group

OAK RIDGE NATIONAL LABORATORY

2360 Cherahala Boulevard

Knoxville, Tennessee 37932

TEL: (865) 946-1467

FAX: (865) 946-1262

EMAIL: liangz@ornl.gov

<http://peemrc.ornl.gov>

2013 PV System Symposium

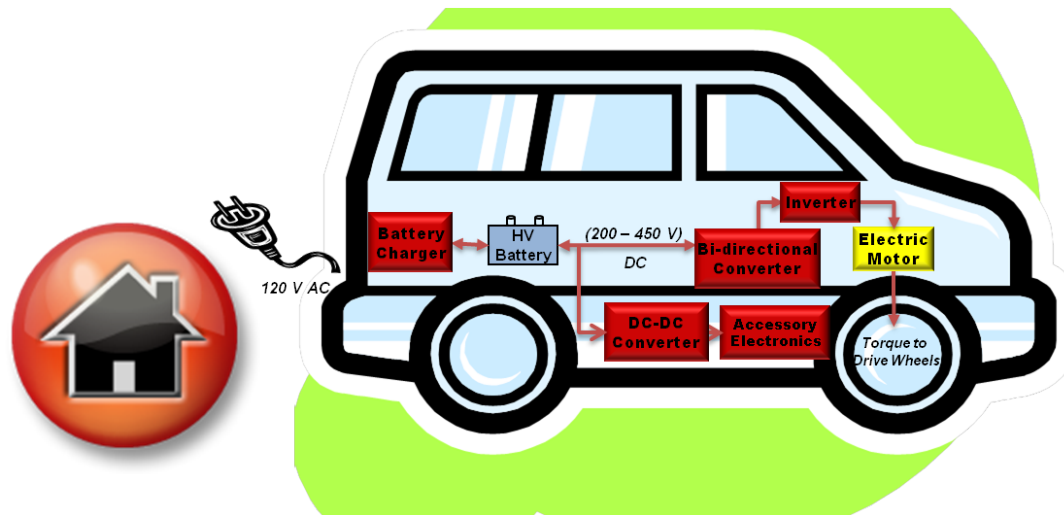
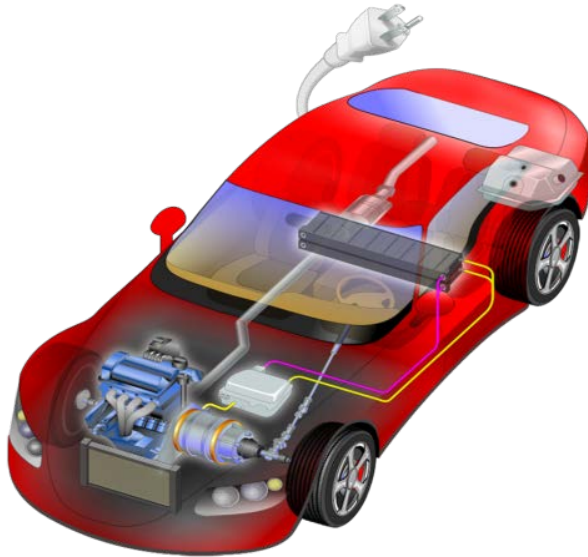
April 30, 2013, Santa Clara, CA



Outline

- Introduction
 - ***Power Electronics in Electric Drive Vehicles***
 - ***Automotive Power Electronics Module Operation***
 - ***Automotive Power Module Packaging***
- High Reliability Power Module Packaging
 - ***Packaging Materials***
 - ***Structure Optimization***
 - ***Process Innovation***
- Emerging Automotive Power Module Packaging
 - ***200°C Si Power Module***
 - ***Planar-Bond -All (PBA) Power Module***
 - ***Advanced All-SiC power module***
- Summary

Power Electronics in xEVs



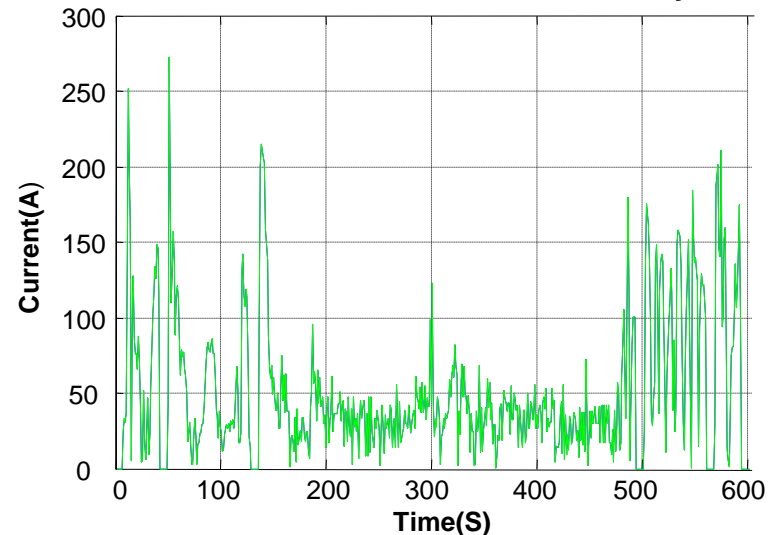
Power Electronics Modules in xEVs

**Typical Traction Drive Requirements: 55 kW peak power for 18 sec;
30 kW continuous power;
15-year life**

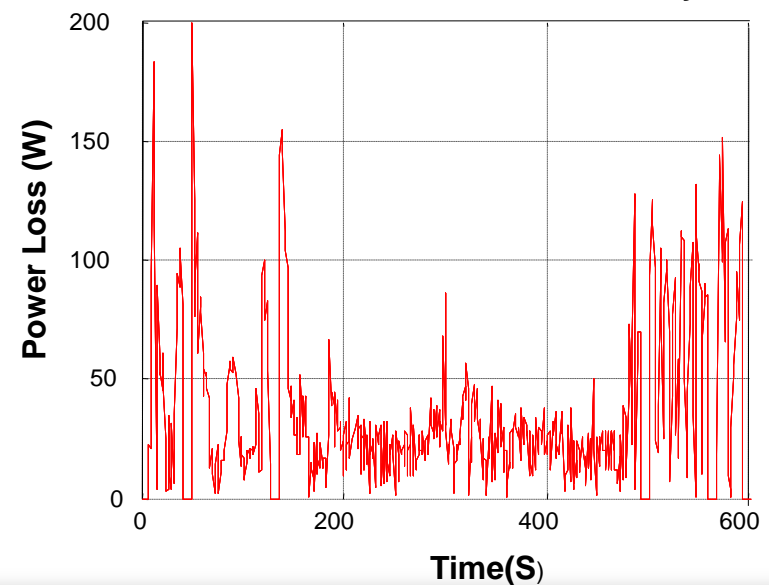
Temperature / Environment

**Ambient air: -40°C to 135°C
Coolant water: -40°C to 105°C
Junction: -40°C to 175°C
Vibration: 10g
Shock: 50g**

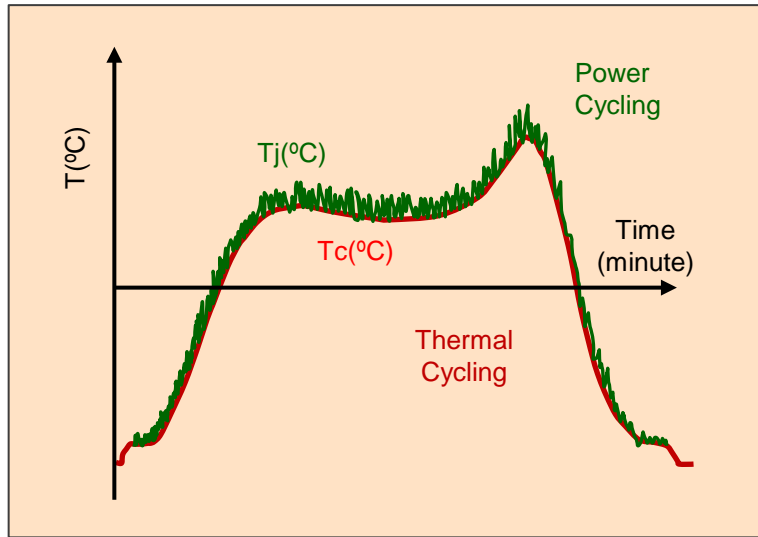
Current Profile Under US06 Drive Cycle



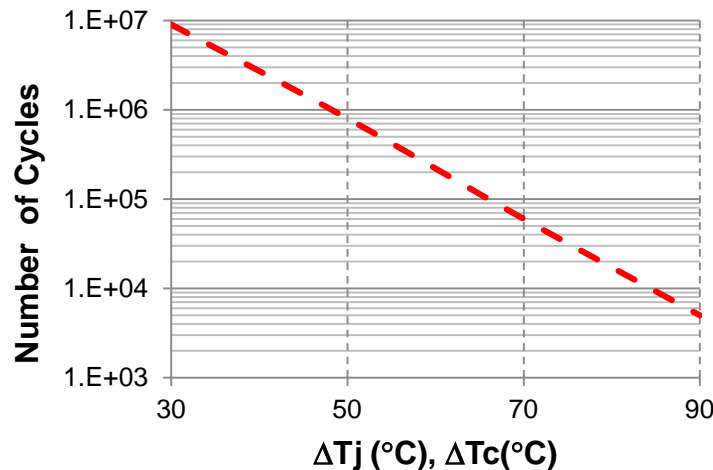
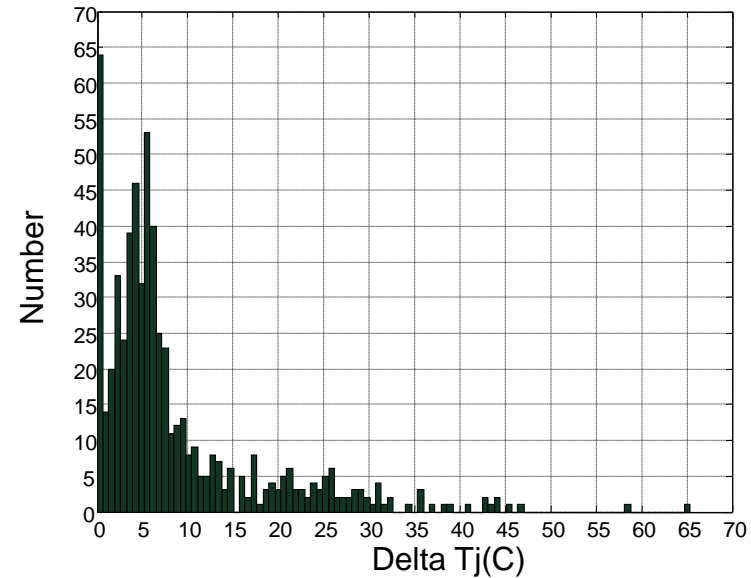
Power Loss Profile Under US06 Drive Cycle



Automotive Power Module Reliability



Device Delta Tj Profile Under US06 Drive Cycle



$$LifetimeConsumption = \sum_{i=1}^{Max} \frac{N_i(\Delta T_{j_i})}{N_f(\Delta T_j)}$$

- Power Derating
- Advanced Semiconductors and Advanced Packaging

Comprehensive Evaluation

Semiconductor Characterization

$$V_{ce} = V_0 + r^* J = V_0 + r^* (I/S)$$

$$E_{\text{switching}} = u^* J^2 + w^* J$$

Thermal characterization

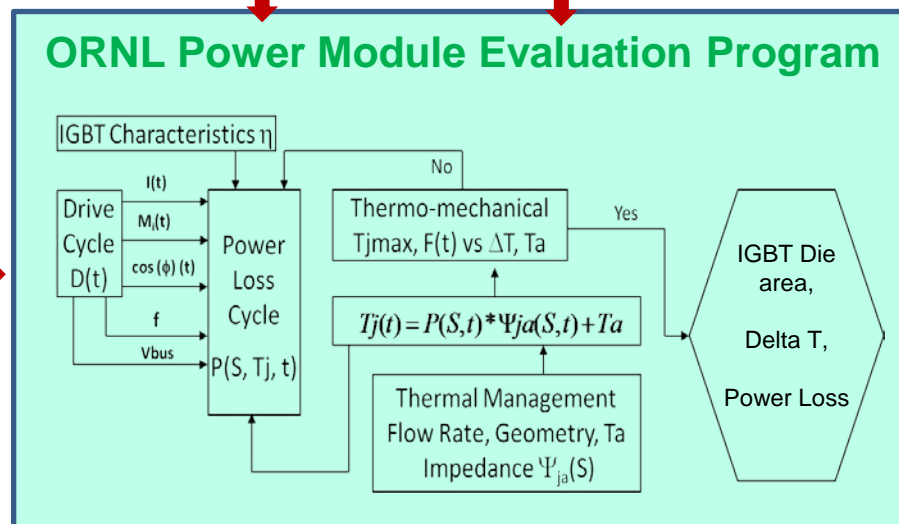
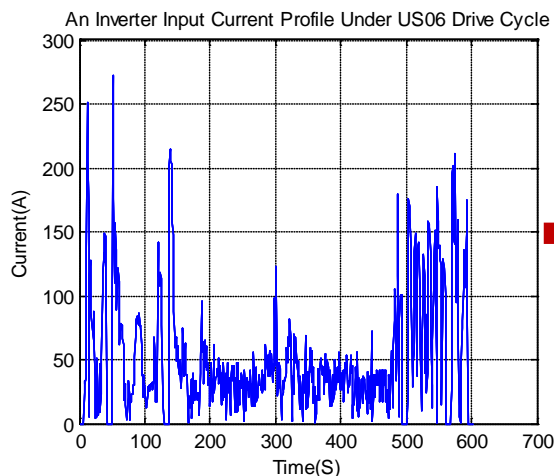
$$\theta_{ja} = \alpha * S^{-\beta}$$

Electrical Characterization

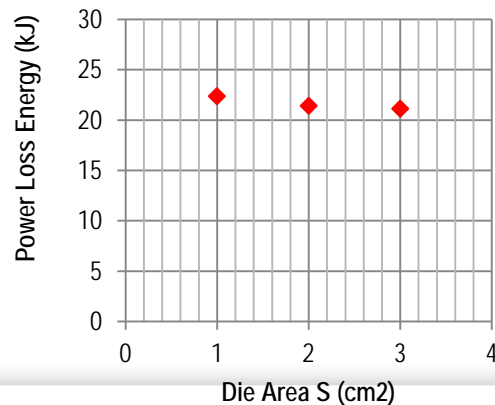
$$L_p, R_p$$

Reliability Characterization

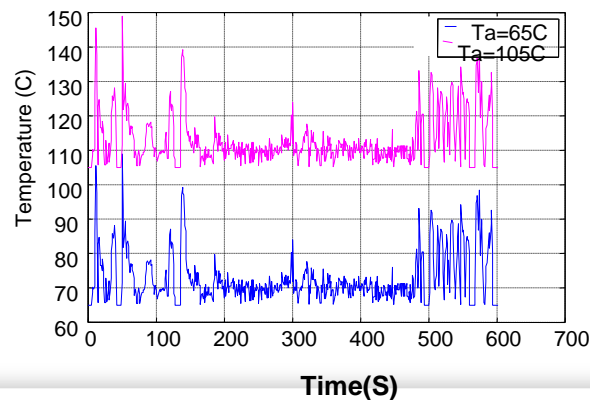
$$N_f = \alpha \cdot \left(\frac{1}{T_j - T_a} \right)^\beta \cdot \exp(E_a / kT_m)$$



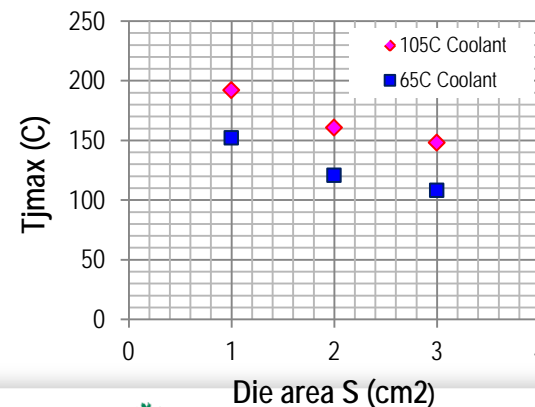
IGBT E-S Curve



IGBT Temperature Profile

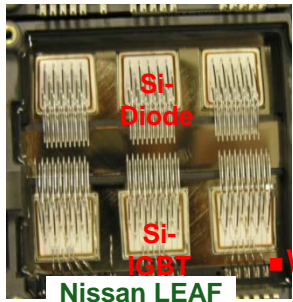


IGBT Tjmax-S Curve

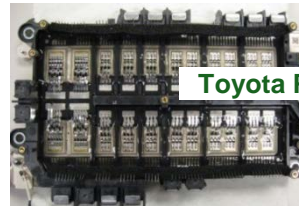
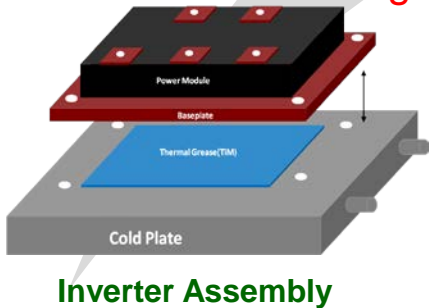


Si Module Packaging Status and Trend

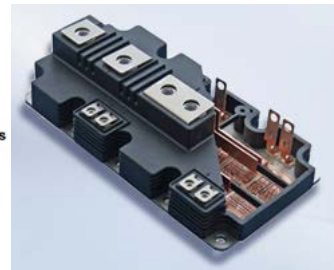
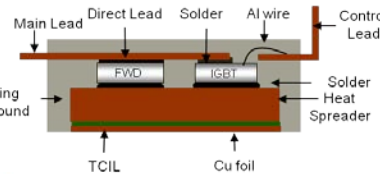
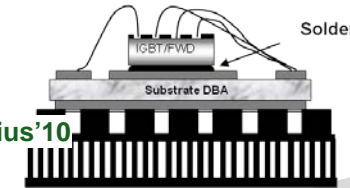
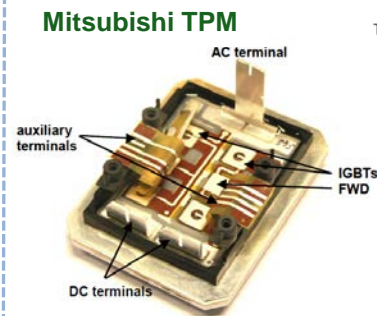
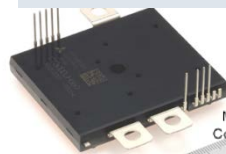
$$\frac{\$}{kW} \propto \frac{S_{Die\ Area}}{P} = \frac{(1-\eta) \cdot \theta_{ja,sp}}{(T_j - T_a)}$$



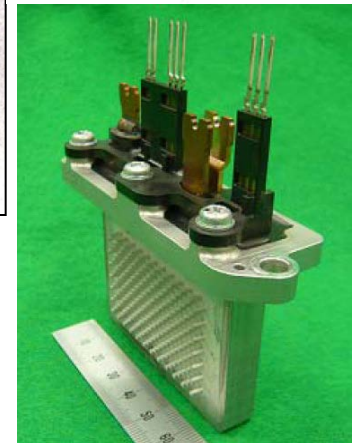
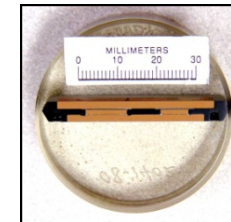
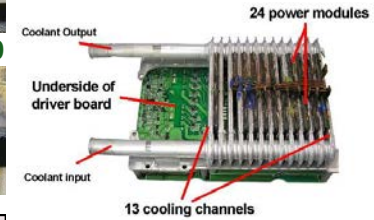
- Gen_I**
- Wire Bond
 - Single Side Interfacial Cooling



- Gen_II**
- Planar Bond
 - Integrated Cooling
 - Reliability Enhancement



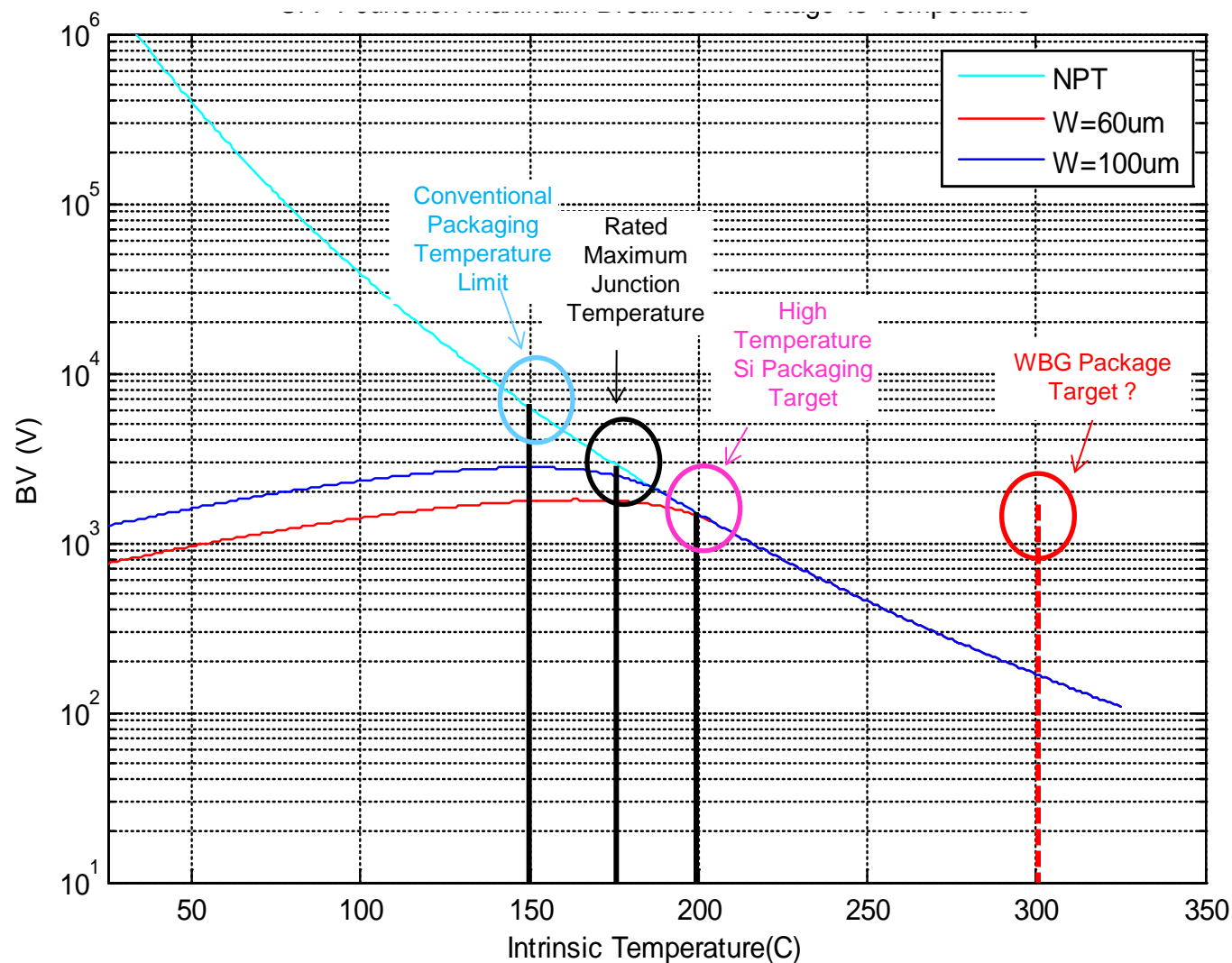
- Gen_III**
- Dual Planar Bond
 - Double Sided Cooling
 - Integrated Double Sided Cooling



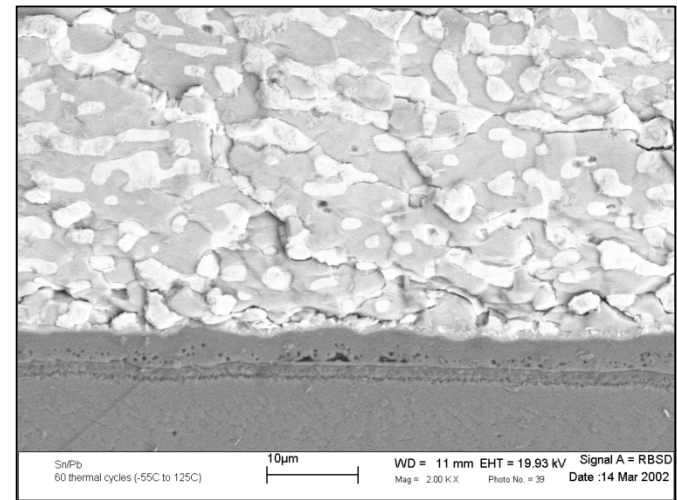
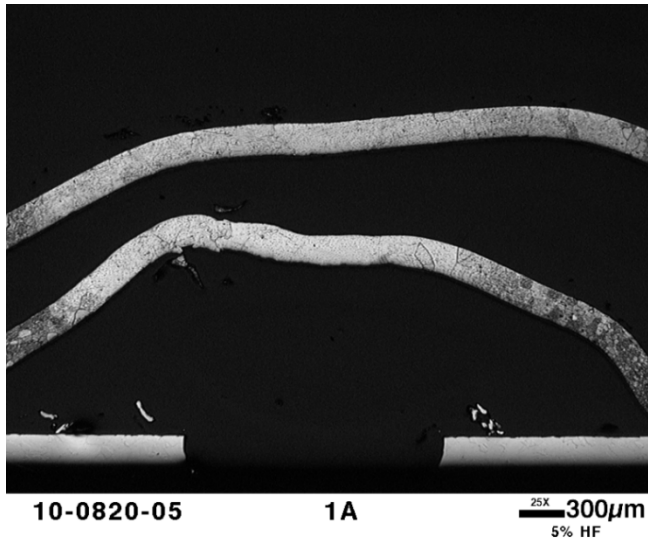
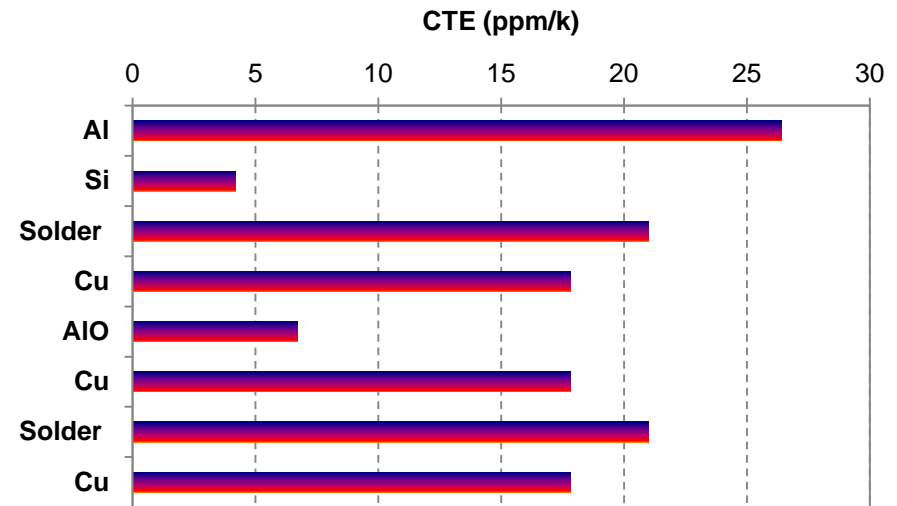
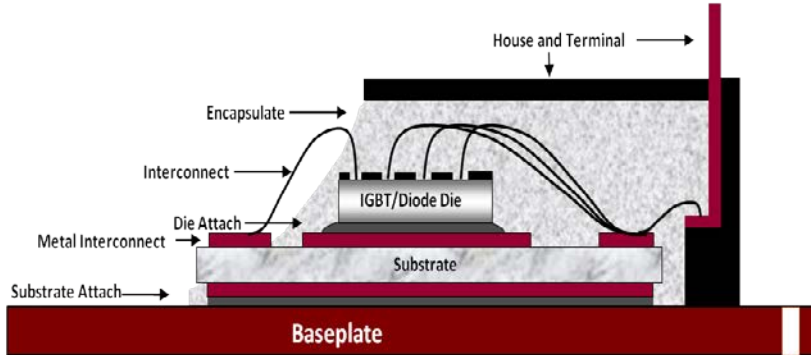
Outline

- Introduction
 - *Power Electronics in Electric Drive Vehicles*
 - *Automotive Power Electronics Module Operation*
 - *Automotive Power Module Packaging*
- High Reliability Power Module Packaging
 - **Packaging Materials**
 - **Structure Optimization**
 - **Process Innovation**
- Emerging Automotive Power Module Packaging
 - *200°C Si Power Module*
 - *Planar-Bond -All (PBA) Power Module*
 - *Advanced All-SiC power module*
- Summary

Operation Temperature of Power Module



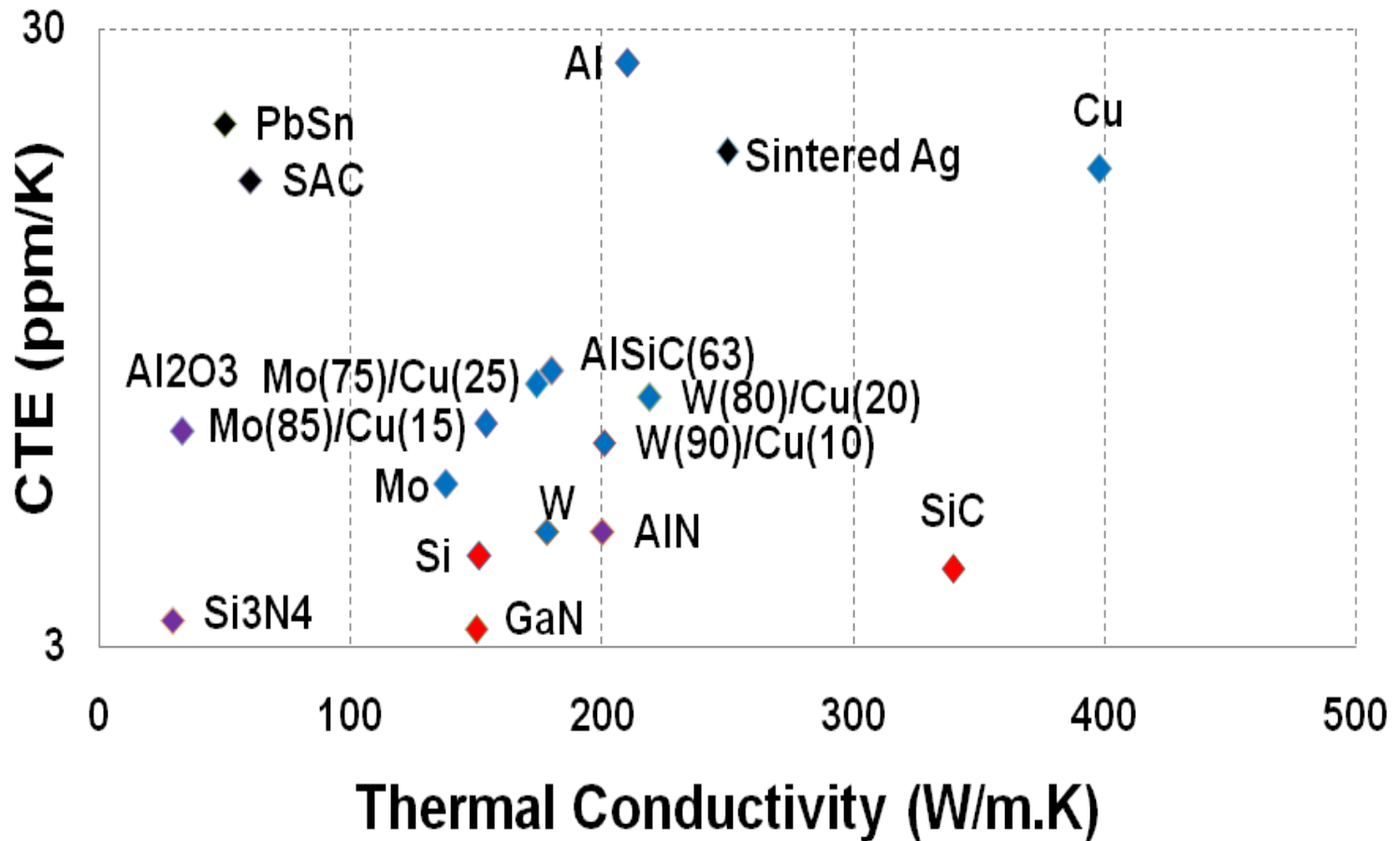
Failure Mechanism: Thermal Expansion and Fatigue



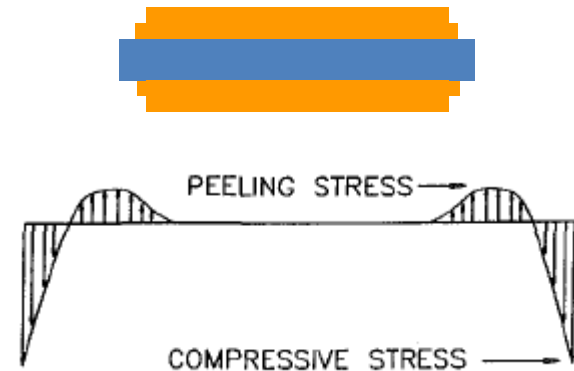
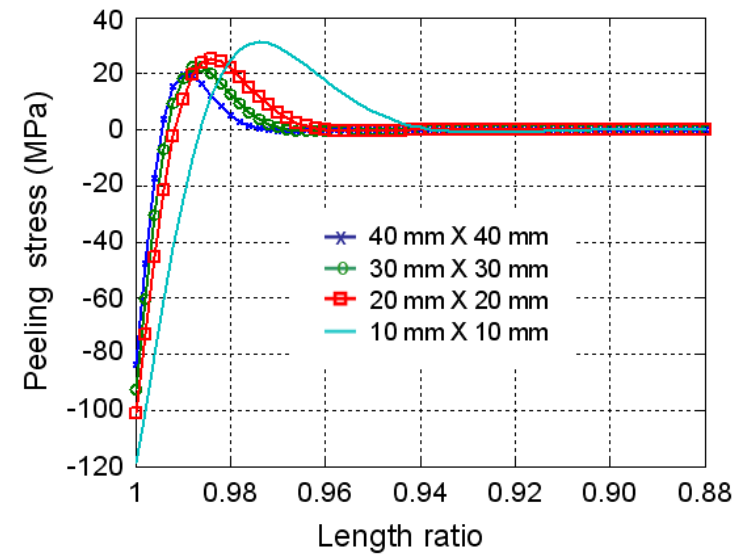
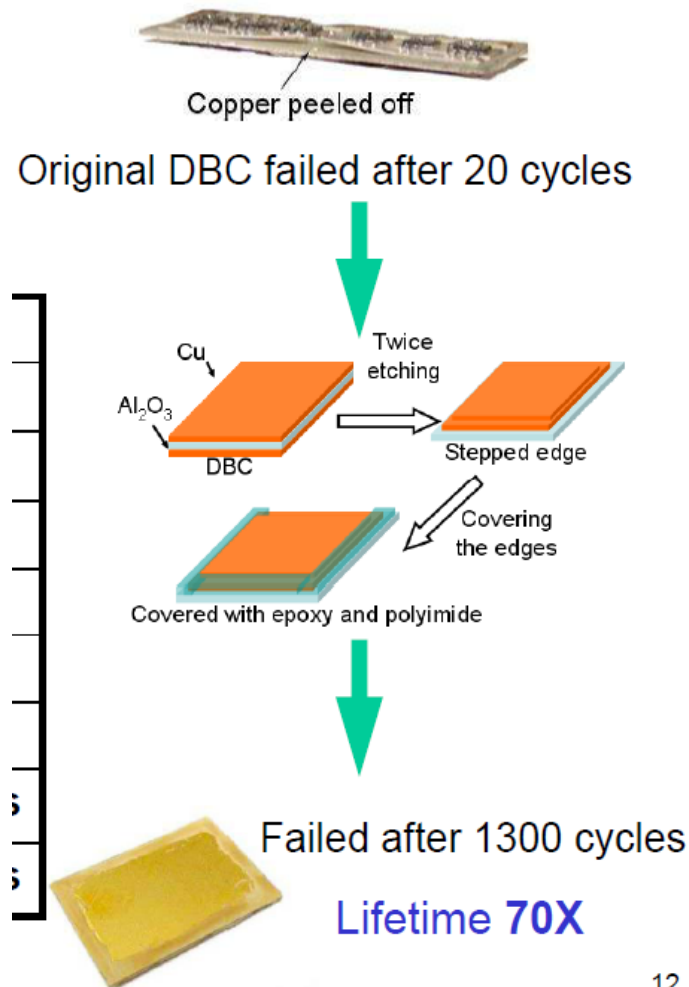
http://www.ornl.gov/sci/propulsionmaterials/pdfs/FY10_Qtr3.pdf

Dimos Katsis, Ph D dissertation, Virginia Tech

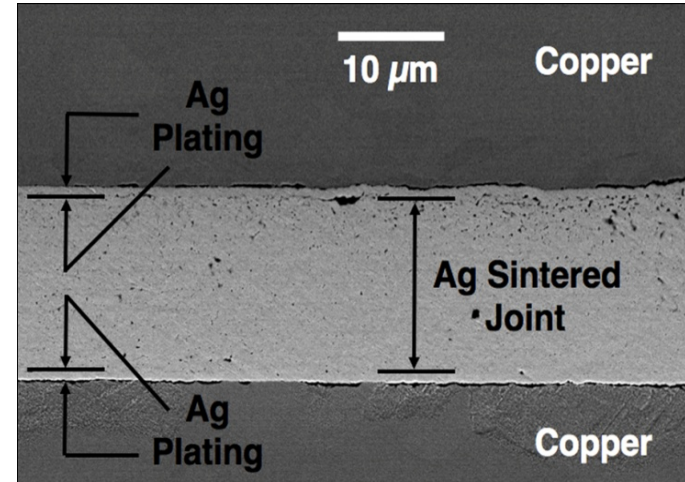
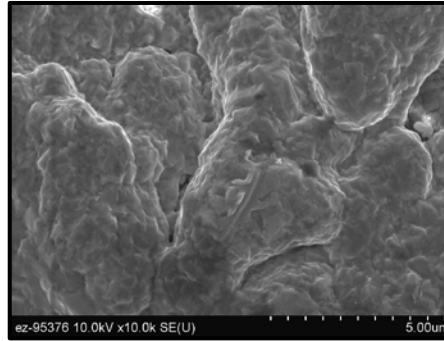
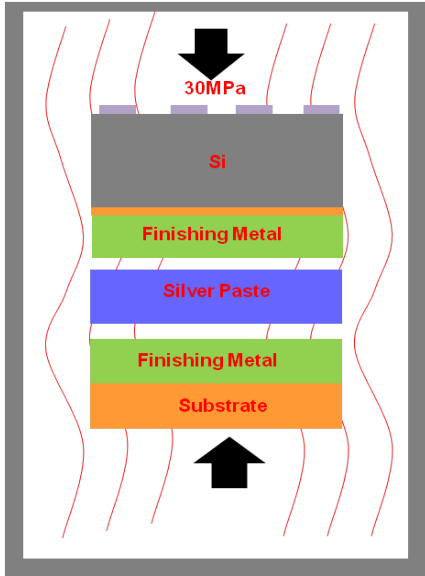
Power Module Packaging Materials



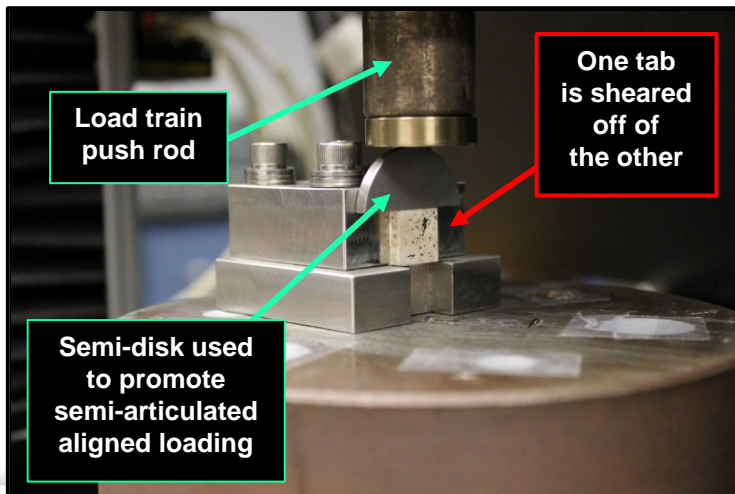
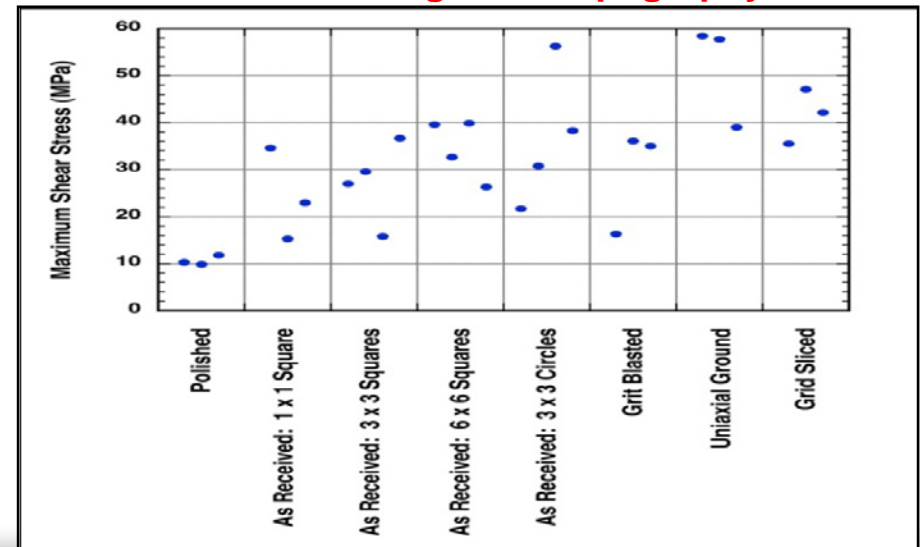
High Reliability Packaging: Structure Optimization



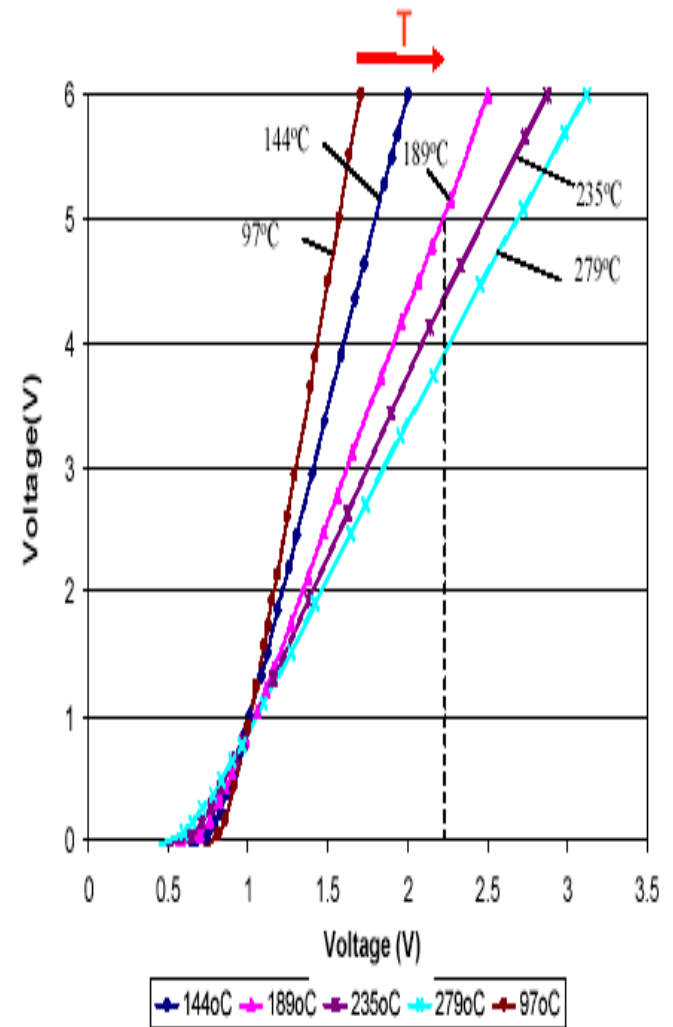
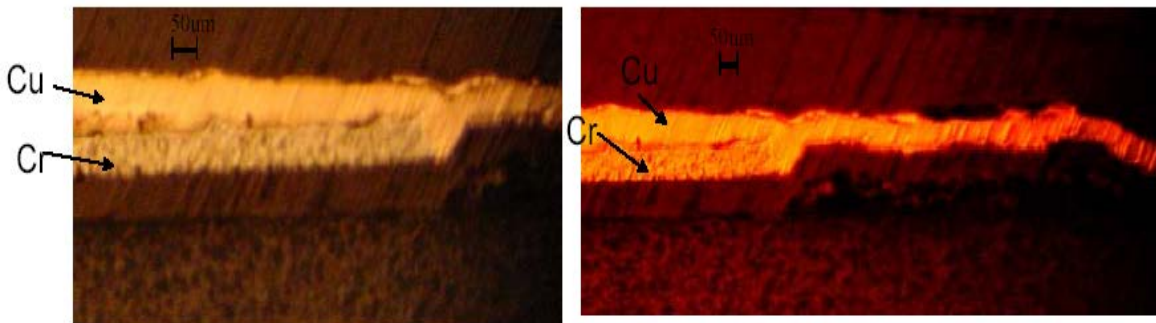
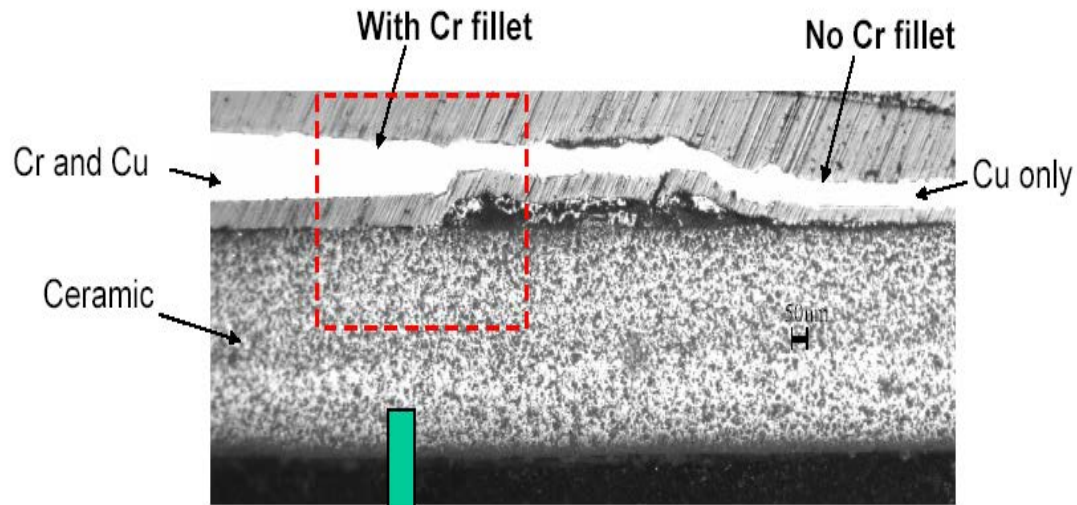
High Reliability Packaging: Ag Sintering Die Attach



Bond Strength vs. Topography



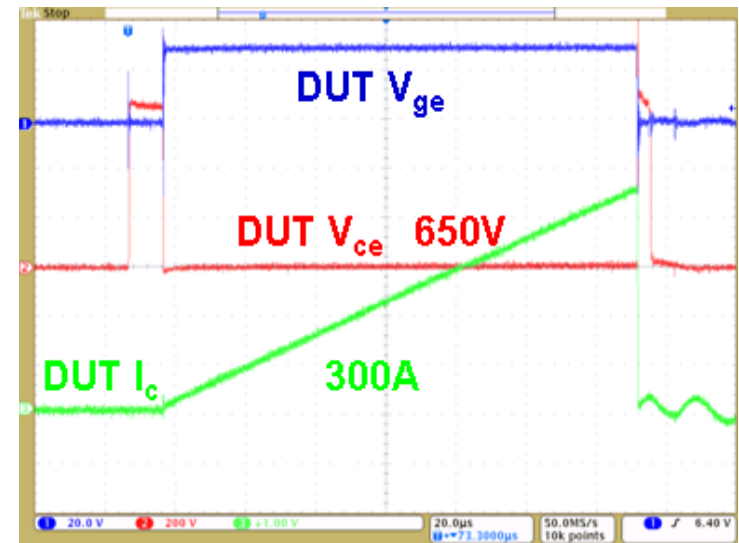
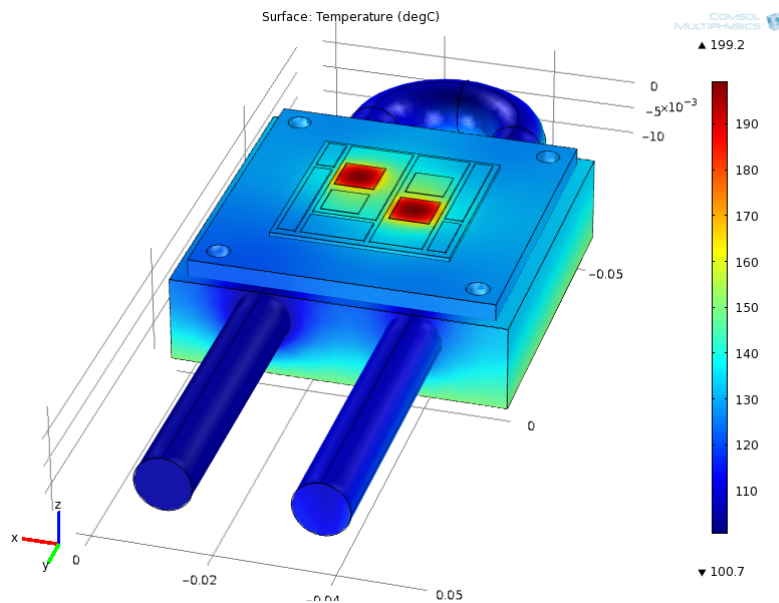
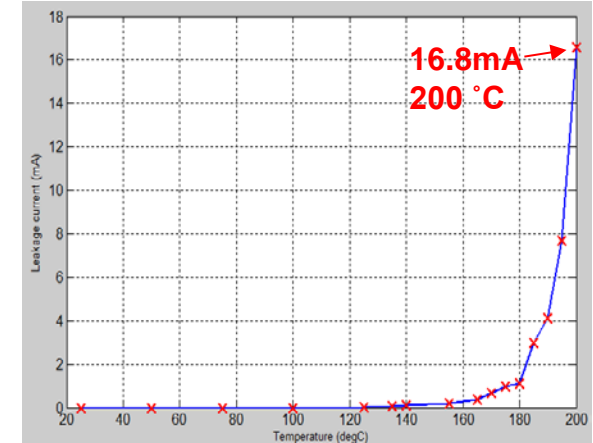
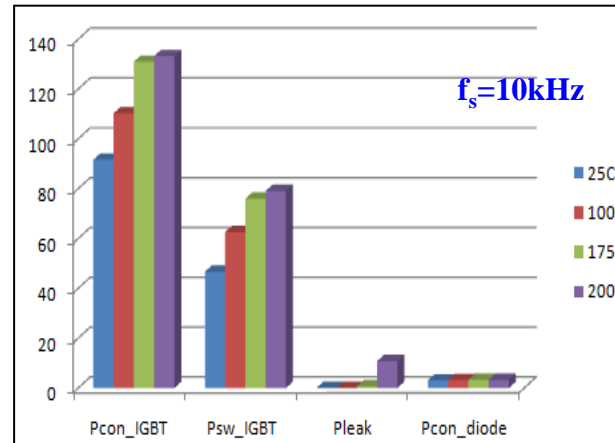
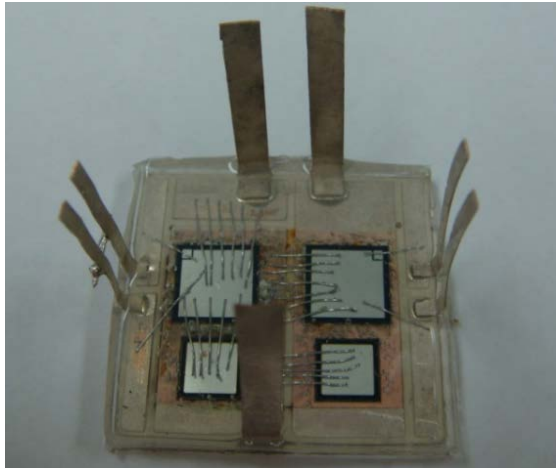
Complex Metallization Interconnection



Outline

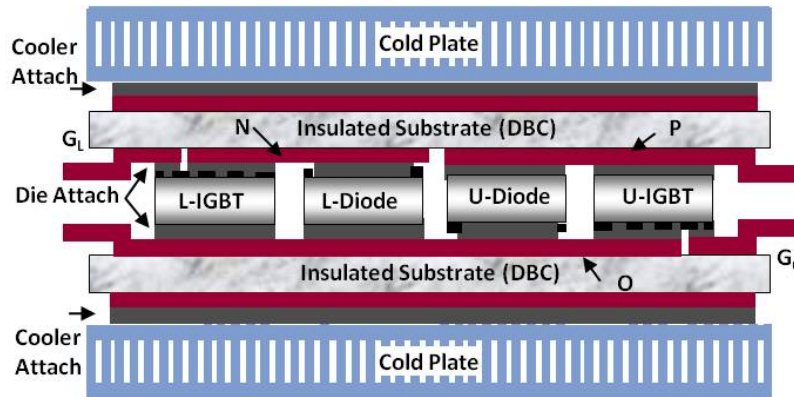
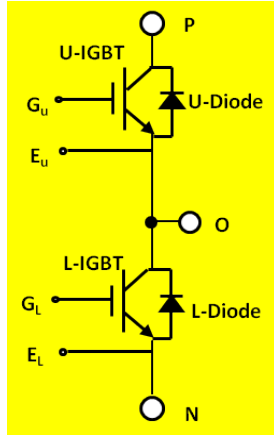
- Introduction
 - *Power Electronics in Electric Drive Vehicles*
 - *Automotive Power Electronics Module Operation*
 - *Automotive Power Module Packaging*
- High Reliability Power Module Packaging
 - *Packaging Materials*
 - *Structure Optimization*
 - *Process Innovation*
- Emerging Automotive Power Module Packaging
 - **200°C Si Power Module**
 - **Planar-Bond -All (PBA) Power Module**
 - **Advanced All-SiC power module**
- Summary

200°C Si IGBT Power Module



Latch-up current test at 250°C

New Concept: Planar Bond All Integrated Power Module

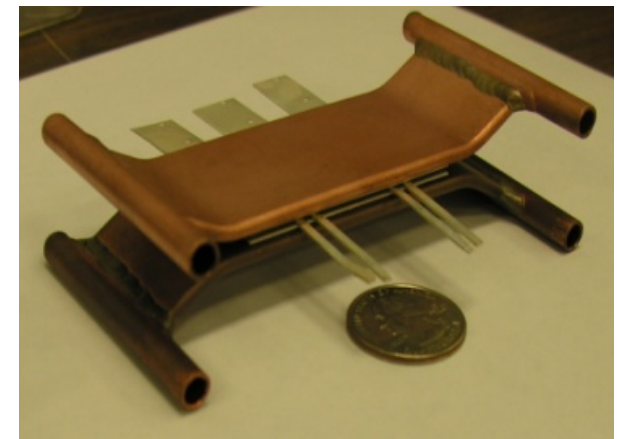
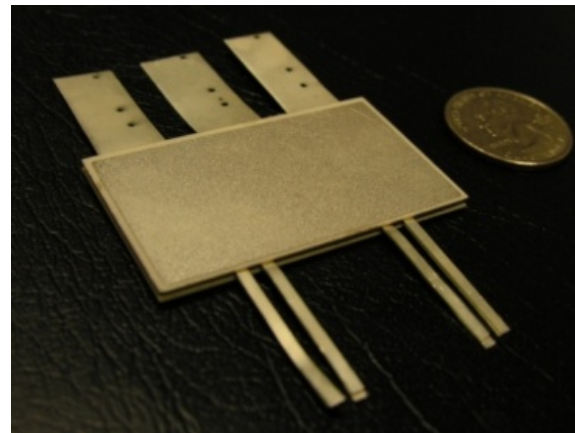
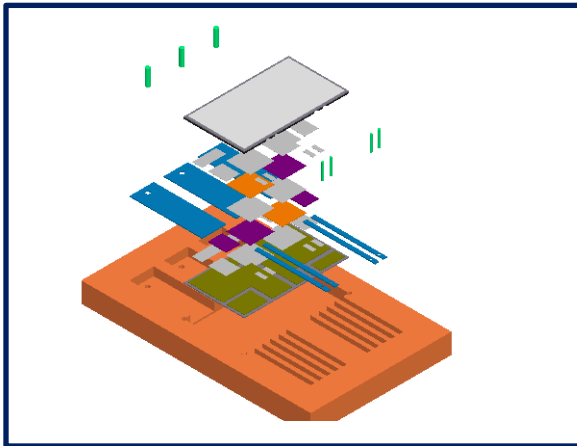


❖ *3-D, Planar Power Interconnection*

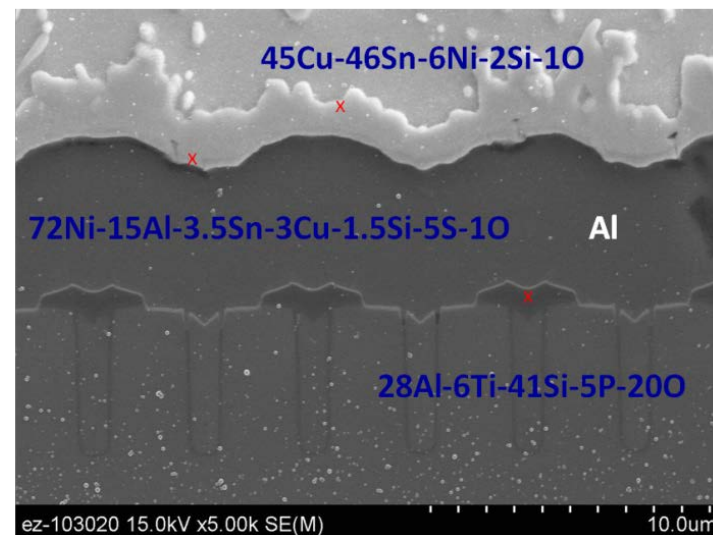
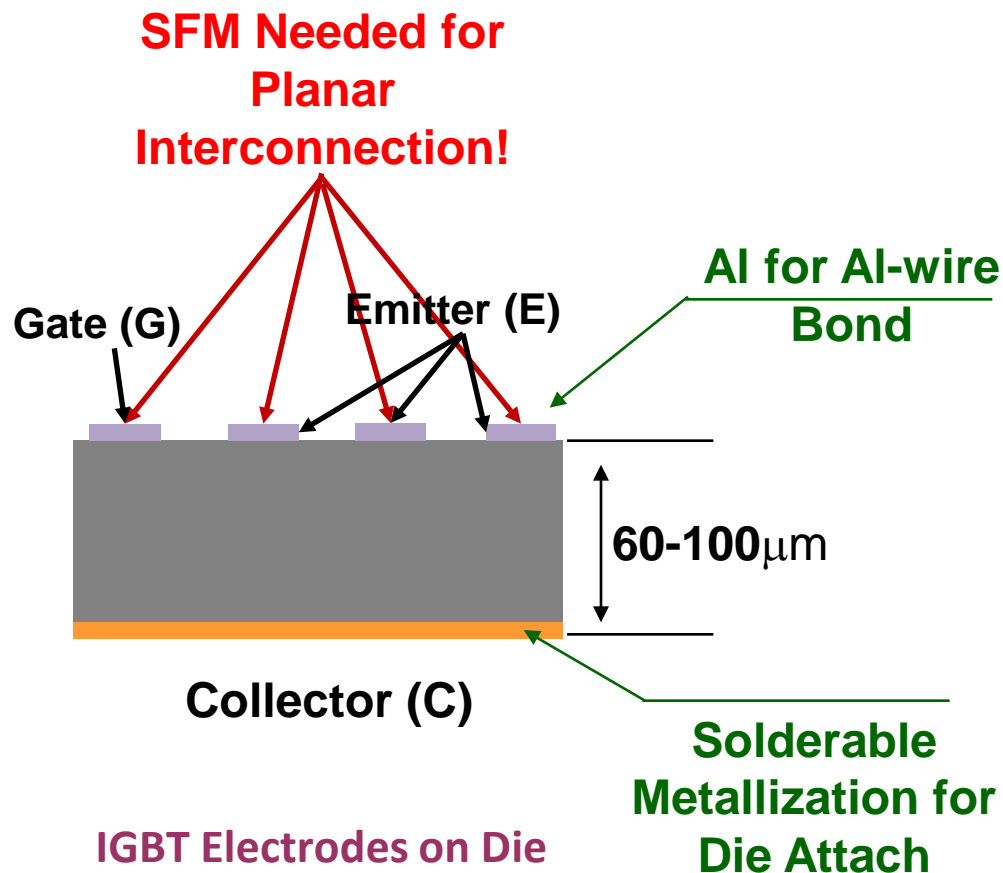
❖ *Integrated, Double Sided Cooling*

❖ *Symmetrically Mechanical Structure*

❖ *Simplified Manufacture*



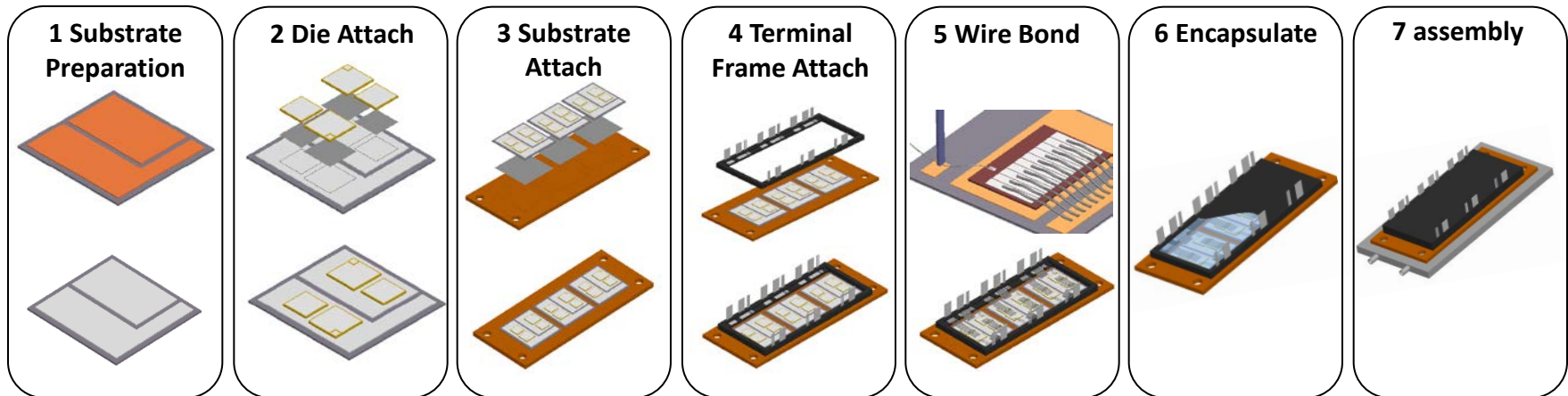
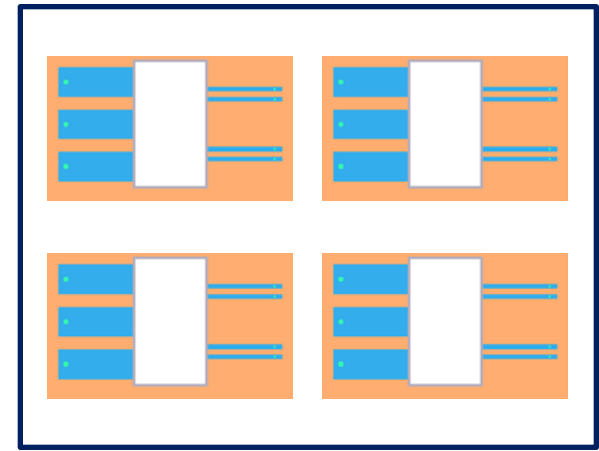
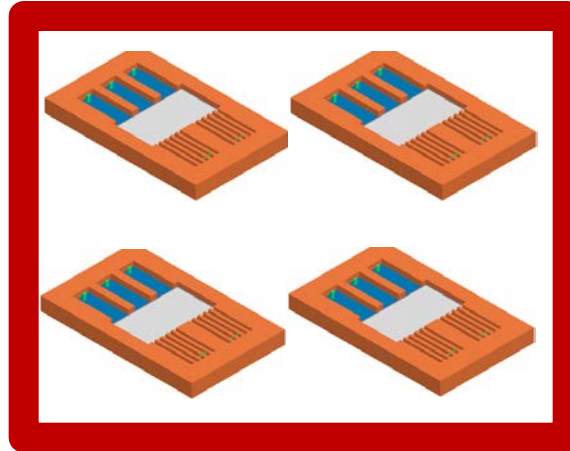
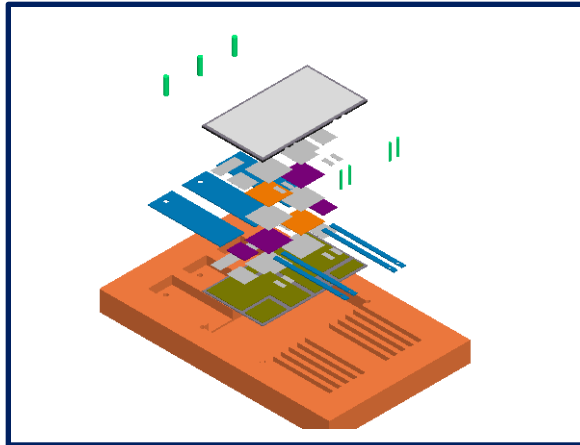
Solderable Front Metallization



Microstructure View of a SFM IGBT Package

Develop New Packaging Process Technology

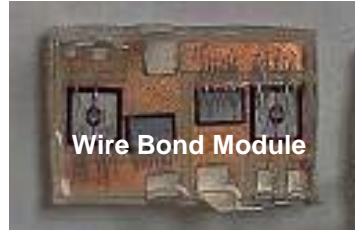
*Planar_Bond_All**



Wire Bond Packaging

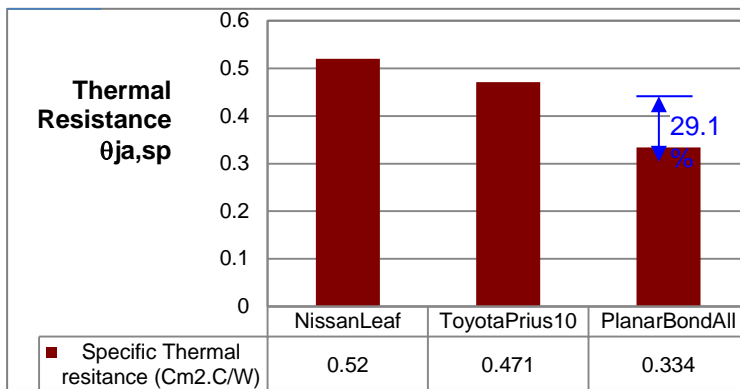
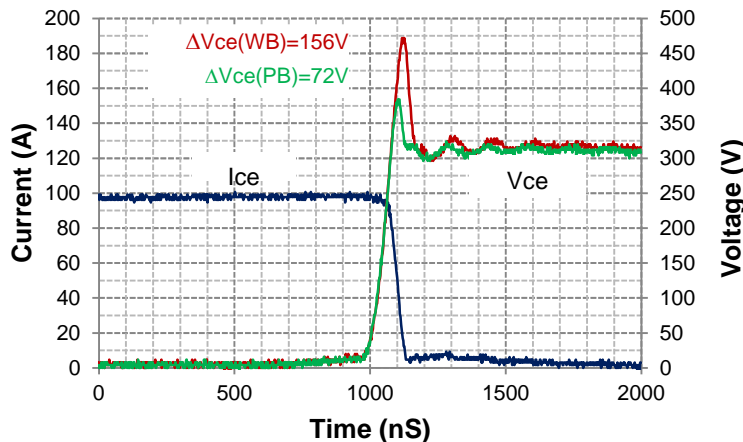
***Patent Pending: US2013/0020694**

PBA Power Module



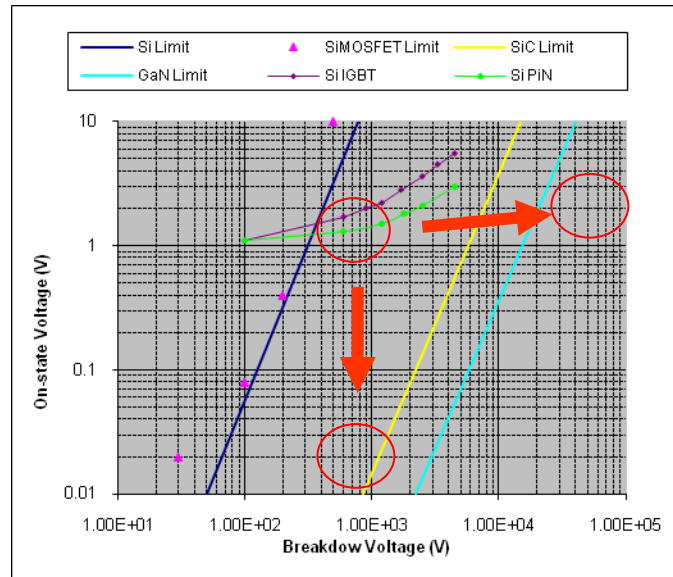
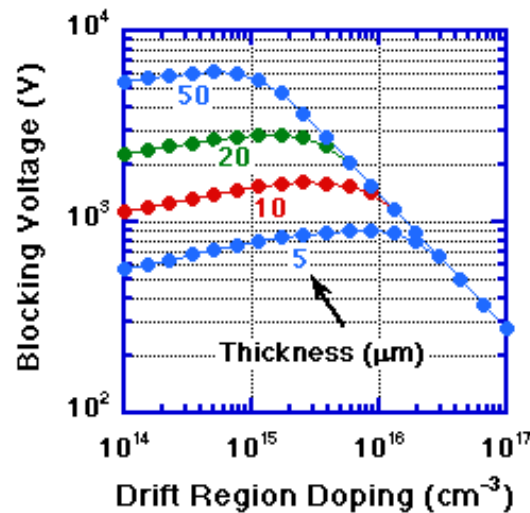
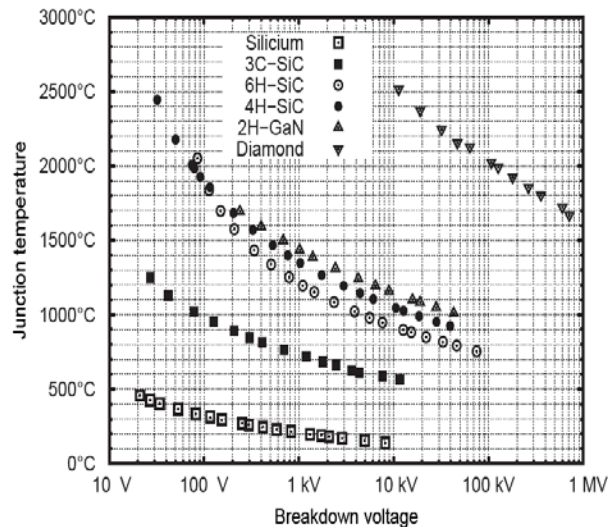
Advancement of PBA packaging technology and power modules:

- ✓ Decreased package thermal resistance by 30%;
- ✓ Decreased package parasitic electrical inductance by 3/4th, and electric resistance by 90%;
- ✓ Reduced the major packaging manufacturing steps from five (5) to two (2);
- ✓ Achieved more than 30% volume, and weight reduction.



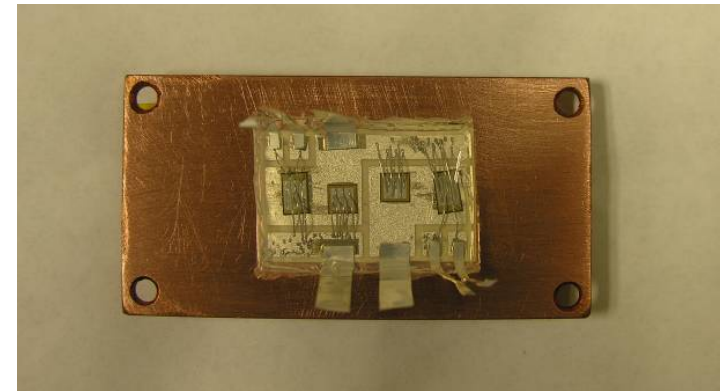
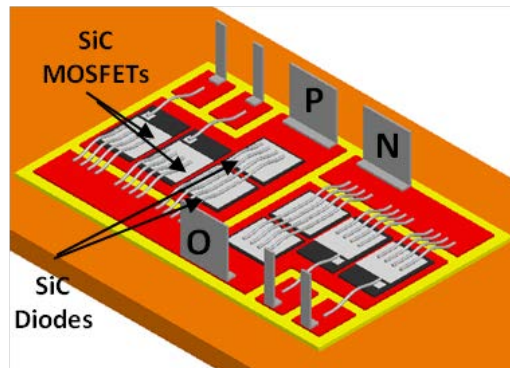
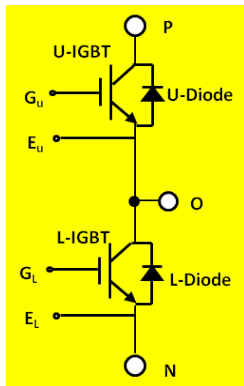
WBG Power Semiconductors

Property	Si	GaAs	SiC	GaN	Diamond
Bandgap, E_g (ev)	1.12	1.43	3.26	3.45	5.45
Breakdown Electric Field E_c (kV/cm)	300	400	2,200	2,000	10,000
Intrinsic Carrier Concentration n_i (cm ⁻³)	9.65E9	1.8E6	1.6E-6	1E-7	1E-27
Electron Mobility μ_n (cm ² /V•s)	1,500	8,500	500-1,000	1,250	2,200
Hole Mobility μ_p (cm ² /V•s)	600	400	100-115	850	850
Dielectric Constant ϵ_r	11.9	13.1	10.1	9	5.5
Thermal Conductivity κ (W/cm•K)	1.5	0.46	4.9	1.3	22
Saturated Electron Drift Velocity v_{sat} (10 ⁷ cm/s)	1	1	2	2.2	2.7

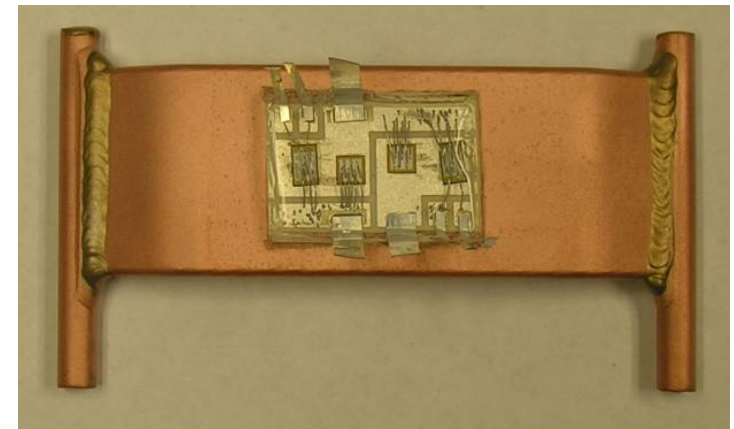
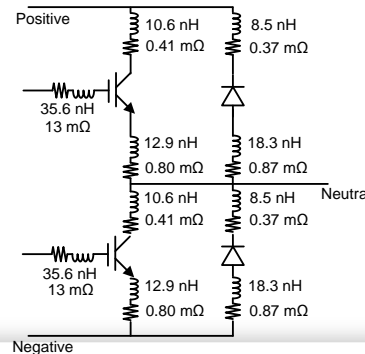
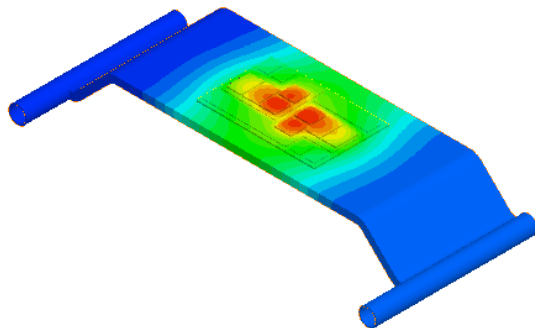
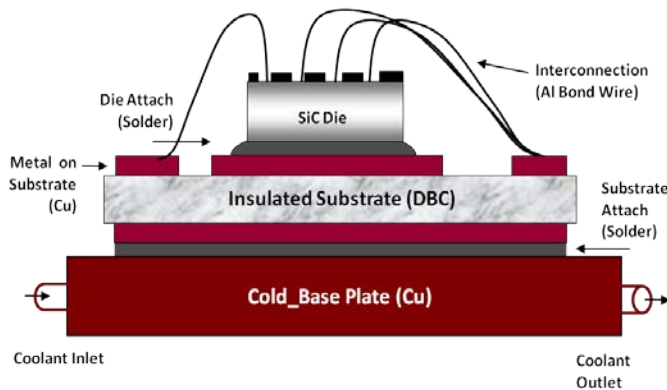


100th Conduction Loss; 100X Voltage Blocking; 10th Switching Loss.

All-SiC Phase Leg Module Packaging

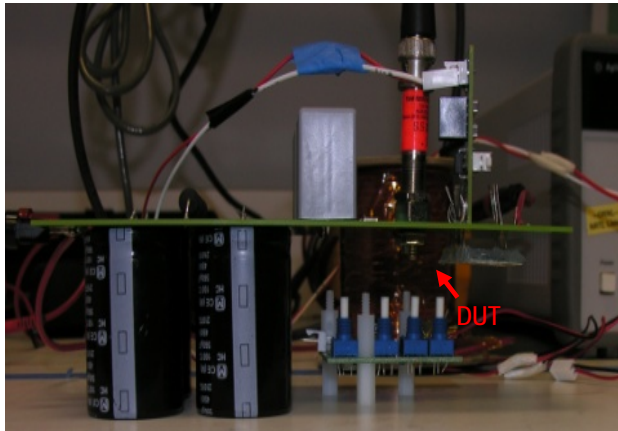


SiC Power Module with Conventional Cooling



SiC Power Module with Integrated Cooling

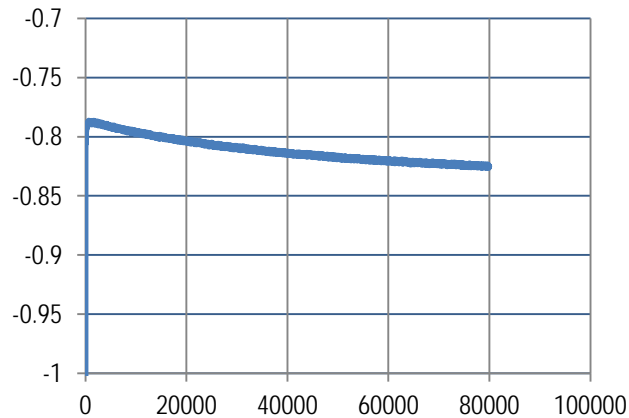
Characterization of SiC Modules



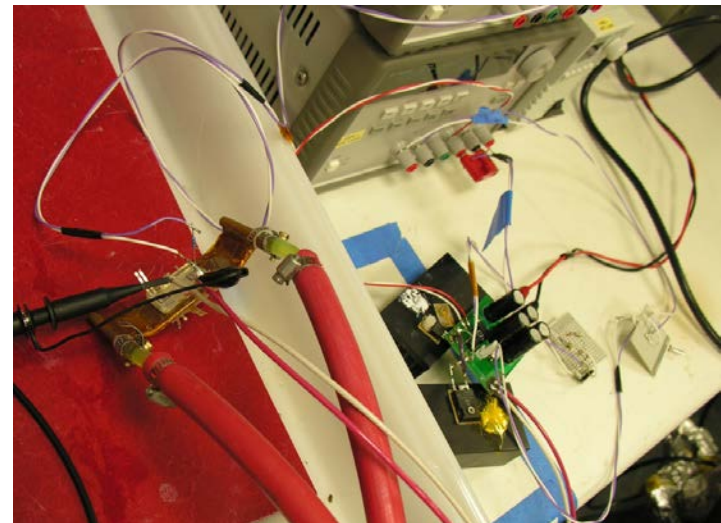
SiC module under electrical testing



SiC module Switching Waveforms

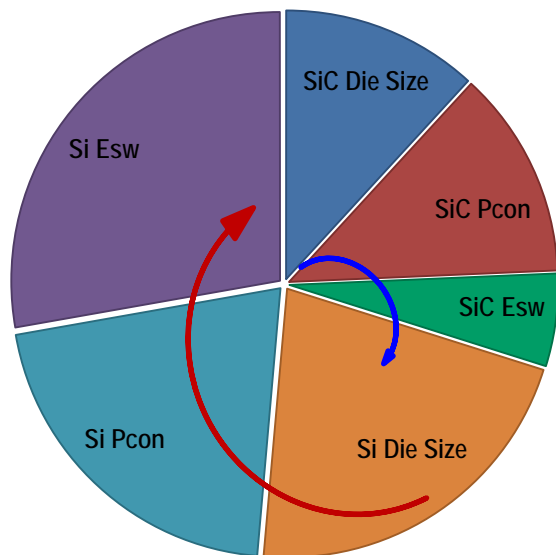


V_f decay of body diode in SiC MOSFET during cooling down phase

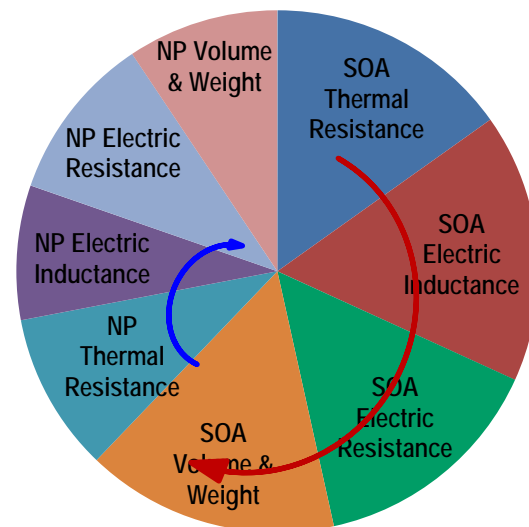


Packaged SiC module in thermal test setup

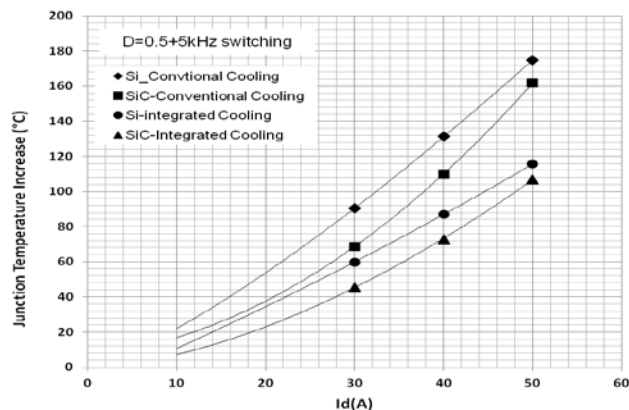
Module Performance Evaluation



SiC and Si Comparison



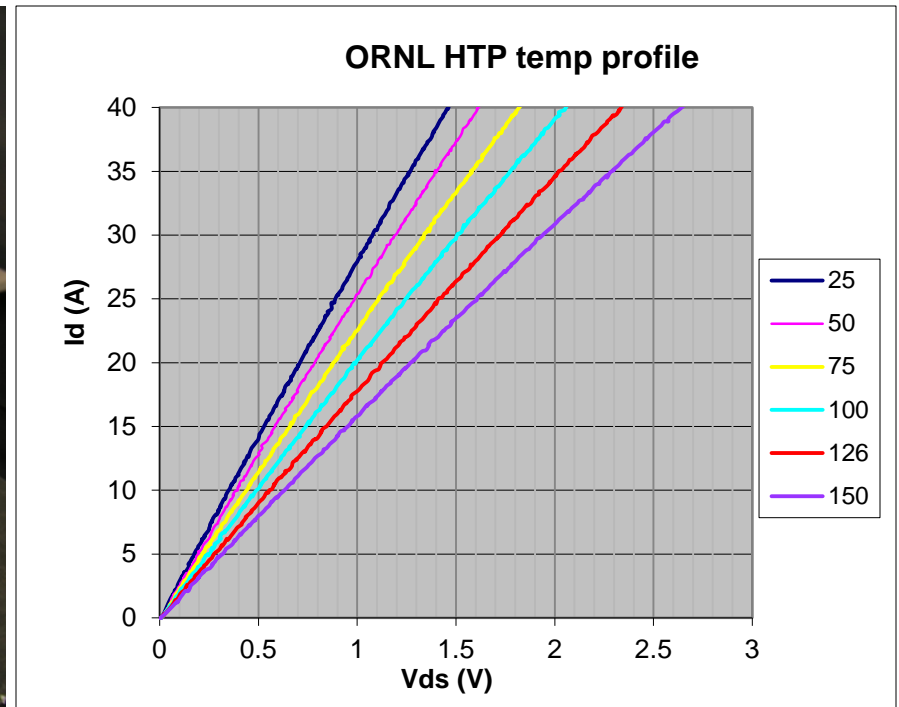
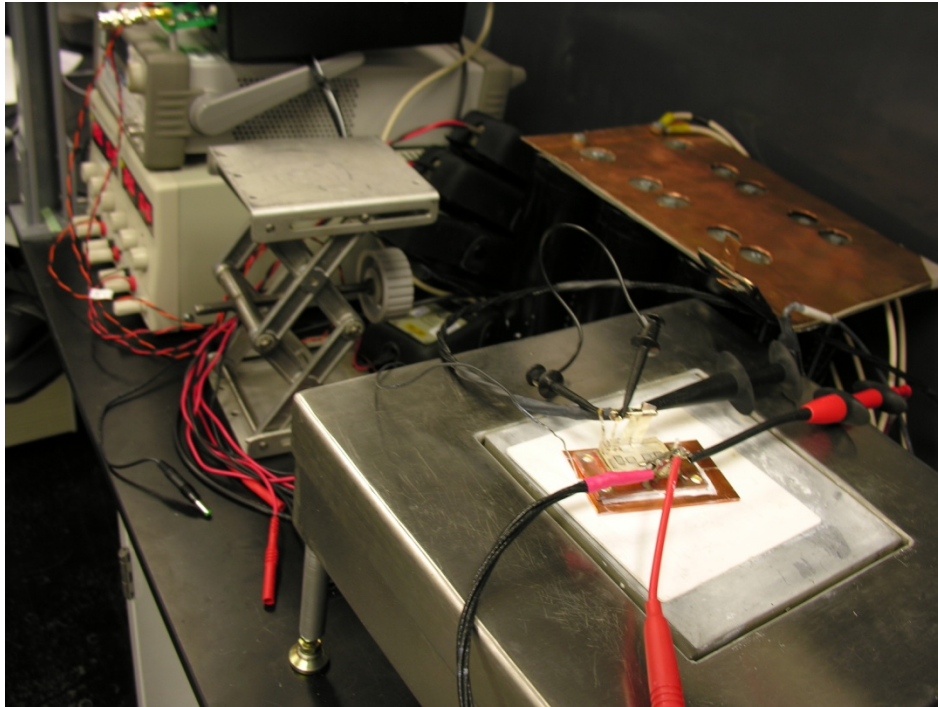
Packaging Comparison



Current density allowed for different power semiconductor and cooling combinations at $\Delta T_j = 100^\circ\text{C}$ for a typical operation ($D=0.5$, $f=5\text{kHz}$)

Item	Si_Con. Cooling	SiC_Con. Cooling	Si_Integ Cooling	SiC_Integ Cooling
Current Density J_d (A/cm ²)	65.35	144.97	97.57	184.98

High Temperature Evaluation of SiC Power Module



Summary

- **Power electronics are critical enabling factors to promoting electric drive vehicles (HEVs and EVs). Power packaging technologies have been advancing, with focus on improvements in cost, reliability, power efficiency and density through structure optimization, material and processing developments.**
- **The State-of-the-Art power modules feature less electrical parasitics, lower thermal resistance and enhanced thermo-mechanical properties to assure the reliability of power electronics in automotive harsh environments.**
- **It is envisioned that more advanced packaging structure/material/process schemes will be developed and integrated for high temperature and high frequency operation of Si and wide bandgap (SiC, GaN) power devices for future automotive applications .**